

FEATURES

- Low noise
- Blue enhanced
- High shunt resistance
- High response

DESCRIPTION

The **PDB-C113** is a blue enhanced PIN silicon photodiode in a photoconductive mode, packaged in a ceramic package.

APPLICATIONS

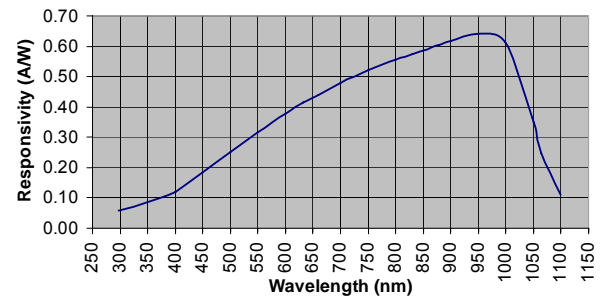
- Instrumentation
- Industrial
- Medical

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		75	V
T _{STG}	Storage Temperature	-40	+100	°C
T _O	Operating Temperature	-40	+90	°C
T _S	Soldering Temperature*		+240	°C

* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	90	110		μA
I _D	Dark Current	V _R = 10V		5	30	nA
R _{SH}	Shunt Resistance	V _R = 10 mV	100	250		MΩ
C _J	Junction Capacitance	V _R = 10 V, f = 1 MHz		60		pF
λ _{range}	Spectral Application Range	Spot Scan	350		1100	nm
R	Responsivity	λ = 450 nm, V _R = 0 V	0.15	0.18		A/W
V _{BR}	Breakdown Voltage	I = 10 μA	75	100		V
NEP	Noise Equivalent Power	V _R = 0V @ λ = 950nm		9x10 ⁻¹⁴		W/√Hz
t _r	Response Time**	RL = 50 Ω, V _R = 0 V		190		nS
		RL = 50 Ω, V _R = 10 V		13		

**Response time of 10% to 90% is specified at 660nm wavelength light.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.